

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1098 2SC1098A

DESCRIPTION

- With TO-202 package
- High Voltage
- High transition frequency

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching
- Suitable for output stages of 5~17W small stereo sets

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

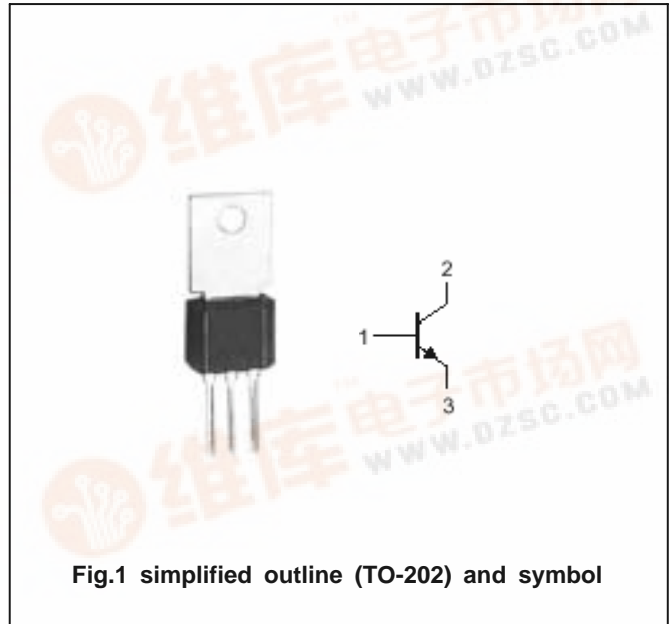


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	70	V
V _{CEO}	Collector-emitter voltage	2SC1098	45	V
		2SC1098A	60	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		5	A
I _B	Base current		0.6	A
P _T	Total power dissipation	T _a =25	1.2	W
		T _C =25	10	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors

2SC1098 2SC1098A

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage		I _C =1.5A; I _B =0.15 A			2.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =1.5A; I _B =0.15 A			2.0	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC1098	I _C =10mA; I _B =0	45			V
		2SC1098A		60			
h _{FE-1}	DC current gain		I _C =20mA ; V _{CE} =5V	20			
h _{FE-2}	DC current gain		I _C =0.5A ; V _{CE} =5V	40		250	
I _{CBO}	Collector cut-off current		V _{CB} =45V ; I _E =0			1.0	μ A
I _{EBO}	Emitter cut-off current		V _{EB} =3V; I _C =0			1.0	μ A
C _{OB}	Output capacitance		I _E =0; V _{CB} =10V; f=1MHz		40		pF
f _T	Transition frequency		I _C =0.1A ; V _{CE} =5V		60		MHz

◆ h_{FE-2} Classifications

N	M	L	K
40-60	50-100	80-160	120-250

Silicon NPN Power Transistors

2SC1098 2SC1098A

PACKAGE OUTLINE

